



20V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON) max}	Package	I _{D max} T _A = +25°C	
201/	60mΩ @ V _{GS} = -4.5V	SOT-23	-4.0A	
-20V	90mΩ @ V _{GS} = -2.5V	501-23	-3.3A	

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- The DMP2065UQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(on)}), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

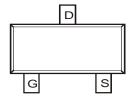
Mechanical Data

Package: SOT23

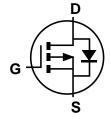
- Package Material: Molded Plastic.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208³
- Terminal Connections: See Diagram
- Weight: 0.009 grams (Approximate)







Top View Pin Configuration



Equivalent Circuit

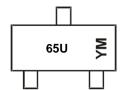
Ordering Information (Note 4)

Part Number	Package	Packaging
DMP2065UQ-7	SOT23	3000/Tape & Reel
DMP2065UQ-13	SOT23	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



65U = Product Type Marking Code YM = Date Code Marking Y = Year (ex: L = 2024) M = Month (ex: 9 = September)

Date Code Key

Year	2020)	2021		2022	20	23	2024		2025	2	2026
Code	Н		ı		J	ŀ	(L		М		N
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ TA = +25°C unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	-20	V
Gate-Source Voltage		Vgss	±12	V	
Drain Current (Note 6) Vgs= -4.5V	T _A = +25°C T _A = +70°C	I _D	-4.0 -3.0	А	
Pulsed Drain Current (Pulse width ≤10µS, Duty	Cycle ≤1%)		IDM	-15	Α

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	0.9	W
Thermal Resistance, Junction to Ambient (Note 5) Steady State		RθJA	138	°C/W
Total Power Dissipation (Note 6)		PD	1.5	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ heta JA}$	83	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

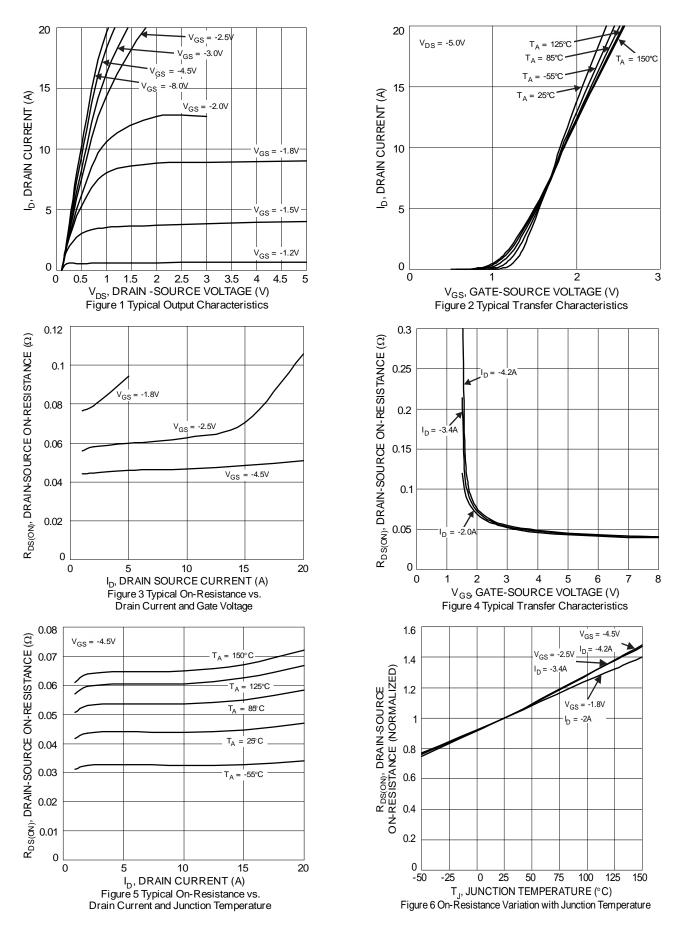
Electrical Characteristics (@ T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BVDSS	-20	_	_	V	V _G S = 0V, I _D = -250μA	
Zero Gate Voltage Drain Current T _J = +25°C	IDSS	_	_	-1.0	μA	V _{DS} = -20V, V _{GS} = 0V	
Gate-Source Leakage	Igss	_		±50	nA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(th)}	-0.5	_	-0.9	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
			41	60		$V_{GS} = -4.5V$, $I_{D} = -4.2A$	
Static Drain-Source On-Resistance	R _{DS} (ON)	_	53	90	mΩ	$V_{GS} = -2.5V$, $I_D = -3.4A$	
			72	113		$V_{GS} = -1.8V$, $I_{D} = -2.0A$	
Diode Forward Voltage	VsD	_	-0.7	-1.1	V	Vgs = 0V, Is = -1A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	808		pF	V 45V V 0V	
Output Capacitance	Coss	_	85		pF	V _{DS} = -15V, V _{GS} = 0V -f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	77		pF	1 - 1.000112	
Gate Resistance	Rg	_	15.2	_	Ω	$V_{GS} = 0V$, $V_{DS} = 0V$, $f = 1.0MHz$	
Total Gate Charge	Q_g	_	10.2		nC		
Gate-Source Charge	Qgs	_	1.3		nC	Vgs = -4.5V, Vps = -4V, Ip = -3.5A	
Gate-Drain Charge	Q_{gd}	_	2.2	_	nC		
Turn-On Delay Time	tD(on)	_	10.8		ns		
Turn-On Rise Time	tr		13.7		ns	$V_{DS} = -4V$, $V_{GS} = -4.5V$,	
Turn-Off Delay Time	t _{D(off)}	_	79.3		ns	$R_L = 4\Omega$, $R_G = 6\Omega$, $I_D = -1A$	
Turn-Off Fall Time	tf	_	34.7	_	ns		

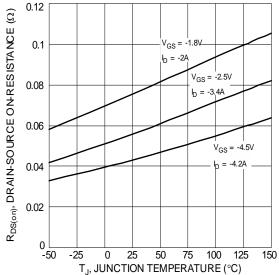
Notes:

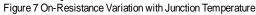
- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1in. square copper plate.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.

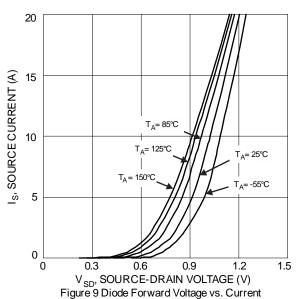


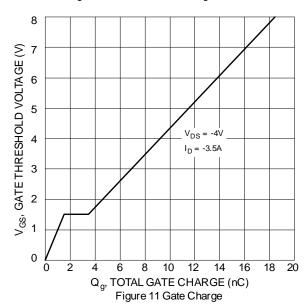












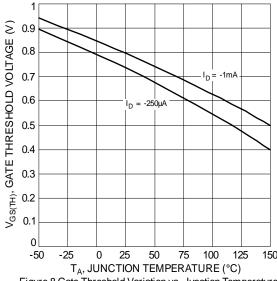
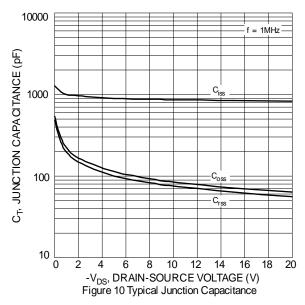
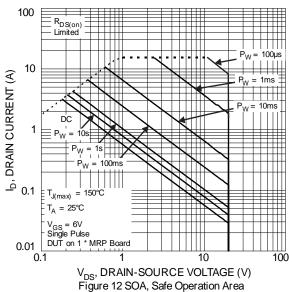


Figure 8 Gate Threshold Variation vs. Junction Temperature







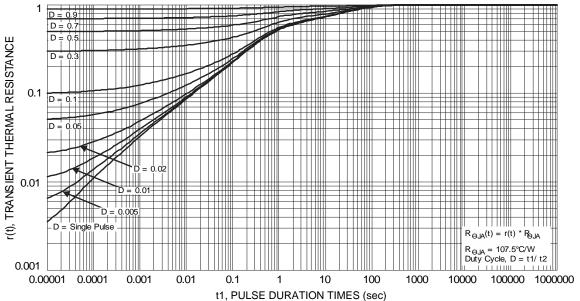


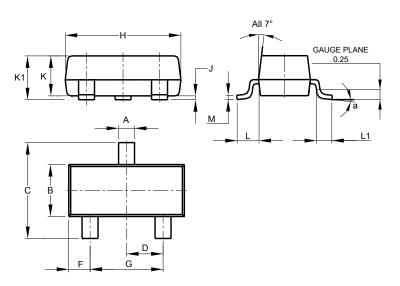
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

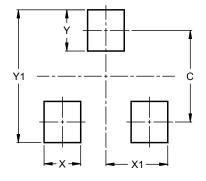


SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
C	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
H	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
١	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
V1	2.0



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